

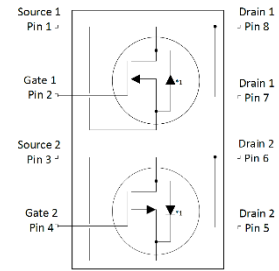
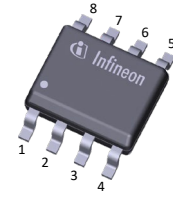
英飞凌MOSFET

PG-DSO-8

OptiMOS™ 3 功率场效应管, 30 V

特性

- 互补型 N 沟道和 P 沟道
- 极低的导通电阻 $R_{DS(on)}$
- 卓越的热阻抗
- 100% 雪崩测试
- 无铅镀层；符合RoHS标准
- 符合 IEC61249-2-21 标准的无卤素



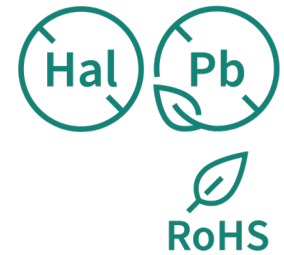
*1: Internal body diode

产品验证

符合 JEDEC 标准。

表 1 主要性能参数

Parameter	Value	Unit
V_{DS} (n-channel)	30	V
$R_{DS(on),max}$ (n-channel)	22	m Ω
I_D (n-channel)	8.4	A
V_{DS} (p-channel)	-30	V
$R_{DS(on),max}$ (p-channel)	28	m Ω
I_D (p-channel)	-8.1	A



Type/Ordering Code	Package	Marking	Related Links
ISA220280C03LMDS	PG-DSO-8	2228C03L	-



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1 最大额定值

除非另有规定， $T_A=25\text{ }^\circ\text{C}$

表 2 最大额定值 (N 沟道)

Parameter	Symbol	Values			Unit	Note/ Test Condition
		Min.	Typ.	Max.		
Continuous drain current ¹⁾	I_D	-	-	8.4 5.3 5.0 6.3	A	$V_{GS}=10\text{ V}, T_C=25\text{ }^\circ\text{C}$ $V_{GS}=10\text{ V},$ $T_C=100\text{ }^\circ\text{C}$ $V_{GS}=4.5\text{ V}, T_C=100\text{ }^\circ\text{C}$ $V_{GS}=10\text{ V}, T_A=25\text{ }^\circ\text{C}, R_{thJA}=90\text{ }^\circ\text{C/W}^2)$
Pulsed drain current ³⁾	$I_{D,pulse}$	-	-	34	A	$T_A=25\text{ }^\circ\text{C}$
Avalanche energy, single pulse ⁴⁾	E_{AS}	-	-	13.2	mJ	$I_D=8.4\text{ A}, R_{GS}=25\text{ }\Omega$
Gate source voltage	V_{GS}	-20	-	20	V	-
Power dissipation	P_{tot}	-	-	2.5 1.4	W	$T_C=25\text{ }^\circ\text{C}$ $T_A=25\text{ }^\circ\text{C}, R_{thJA}=90\text{ }^\circ\text{C/W}^2)$
Operating and storage temperature	T_j, T_{stg}	-55	-	150	$^\circ\text{C}$	-

- 1) 额定值指产品仅具有数据手册指定的绝对最大值，保持外壳温度符合规定要求。其他情况下的温度，n 沟道请参见图 2，p 沟道请参见图 17。需要根据实际环境条件降低等级。
- 2) 器件置于 $40\text{ mm} \times 40\text{ mm} \times 1.5\text{ mm}$ 环氧树脂印刷电路板 FR4 上，配有 6 cm^2 (单层， $70\text{ }\mu\text{m}$ 厚) 铜层面积用于漏极连接。印刷电路板垂直放置在静止空气中。一个开关管工作。
- 3) 详细信息请参见图 3 与 18
- 4) 详细信息请参见图 13 与 28

表 3 最大额定值 (P 沟道)

Parameter	Symbol	Values			Unit	Note/ Test Condition
		Min.	Typ.	Max.		
Continuous drain current ⁵⁾	I_D	-	-	-8.1 -5.1 -4.5 -6.1	A	$V_{GS}=-10\text{ V}, T_C=25\text{ }^\circ\text{C}$ $V_{GS}=-10\text{ V},$ $T_C=100\text{ }^\circ\text{C}$ $V_{GS}=-4.5\text{ V},$ $T_C=100\text{ }^\circ\text{C}$ $V_{GS}=-10\text{ V}, T_A=25\text{ }^\circ\text{C}, R_{thJA}=90\text{ }^\circ\text{C/W}^6)$
Pulsed drain current ⁷⁾	$I_{D,pulse}$	-	-	-32	A	$T_A=25\text{ }^\circ\text{C}$
Avalanche energy, single pulse ⁸⁾	E_{AS}	-	-	13.2	mJ	$I_D=-8.1\text{ A}, R_{GS}=25\text{ }\Omega$
Gate source voltage	V_{GS}	-20	-	20	V	-
Power dissipation	P_{tot}	-	-	2.5 1.4	W	$T_C=25\text{ }^\circ\text{C}$ $T_A=25\text{ }^\circ\text{C}, R_{thJA}=90\text{ }^\circ\text{C/W}^6)$
Operating and storage temperature	T_j, T_{stg}	-55	-	150	$^\circ\text{C}$	-

- 5) 额定值指产品仅具有数据手册指定的绝对最大值，保持外壳温度符合规定要求。其他情况下的温度，n 沟道请参见图 2，p 沟道请参见图 17。需要根据实际环境条件降低等级。
- 6) 器件置于 $40\text{ mm} \times 40\text{ mm} \times 1.5\text{ mm}$ 环氧树脂印刷电路板 FR4 上，配有 6 cm^2 (单层， $70\text{ }\mu\text{m}$ 厚) 铜层面积用于漏极连接。印刷电路板垂直放置在静止空气中。一个开关管工作。



- 7) 详细信息请参见图 3 与18
- 8) 详细信息请参见图 13 与28

2 热特性

表 4 热特性

Parameter	Symbol	Values			Unit	Note/ Test Condition
		Min.	Typ.	Max.		
Thermal resistance, junction - solder point	R_{thJC}	-	-	50	°C/W	-
Thermal resistance, junction - ambient, minimal footprint, steady state	R_{thJA}	-	-	150	°C/W	-
Thermal resistance, junction - ambient, 6 cm ² cooling area, steady state ⁹⁾	R_{thJA}	-	-	90	°C/W	-

⁹⁾ 器件置于40 mm × 40 mm × 1.5 mm 环氧树脂印刷电路板 FR4 上，配有6 cm²（单层，70 μm厚）铜层面积用于漏极连接。印刷电路板垂直放置在静止空气中。一个开关管工作。

3 电气特性

除非另有规定, $T_j=25\text{ }^\circ\text{C}$

表5 静态特性 (N沟道)

Parameter	Symbol	Values			Unit	Note/ Test Condition
		Min.	Typ.	Max.		
Drain-source breakdown voltage	$V_{(BR)DSS}$	30	-	-	V	$V_{GS}=0\text{ V}, I_D=1\text{ mA}$
Gate threshold voltage	$V_{GS(th)}$	1.1	-	2.7	V	$V_{DS}=V_{GS}, I_D=1000\text{ }\mu\text{A}$
Zero gate voltage drain current	I_{DSS}	-	0.1 10	1 100	μA	$V_{DS}=30\text{ V}, V_{GS}=0\text{ V}, T_j=25\text{ }^\circ\text{C}$ $V_{DS}=30\text{ V}, V_{GS}=0\text{ V}, T_j=125\text{ }^\circ\text{C}$
Gate-source leakage current	I_{GSS}	-	10	100	nA	$V_{GS}=20\text{ V}, V_{DS}=0\text{ V}$
Drain-source on-state resistance	$R_{DS(on)}$	-	17 20	22 25	m Ω	$V_{GS}=10\text{ V}, I_D=8.4\text{ A}$ $V_{GS}=4.5\text{ V}, I_D=7\text{ A}$
Gate resistance	R_G	-	1.5	-	Ω	-
Transconductance ¹⁰⁾	g_{fs}	10	20	-	S	$ V_{DS} \geq 2 I_D R_{DS(on)max}, I_D=8.4\text{ A}$

¹⁰⁾ 由设计指定, 未经过生产测试。

表6 静态特性 (P沟道)

Parameter	Symbol	Values			Unit	Note/ Test Condition
		Min.	Typ.	Max.		
Drain-source breakdown voltage	$V_{(BR)DSS}$	-30	-	-	V	$V_{GS}=0\text{ V}, I_D=-1\text{ mA}$
Gate threshold voltage	$V_{GS(th)}$	-1.1	-	-2.7	V	$V_{DS}=V_{GS}, I_D=-1000\text{ }\mu\text{A}$
Zero gate voltage drain current	I_{DSS}	-	-0.1 -10	-1 -100	μA	$V_{DS}=-30\text{ V}, V_{GS}=0\text{ V}, T_j=25\text{ }^\circ\text{C}$ $V_{DS}=-30\text{ V}, V_{GS}=0\text{ V}, T_j=125\text{ }^\circ\text{C}$
Gate-source leakage current	I_{GSS}	-	-10	-100	nA	$V_{GS}=-20\text{ V}, V_{DS}=0\text{ V}$
Drain-source on-state resistance	$R_{DS(on)}$	-	24 32	28 37	m Ω	$V_{GS}=-10\text{ V}, I_D=-8.1\text{ A}$ $V_{GS}=-4.5\text{ V}, I_D=-7\text{ A}$
Gate resistance	R_G	-	8.5	-	Ω	-
Transconductance ¹¹⁾	g_{fs}	8.5	17	-	S	$ V_{DS} \geq 2 I_D R_{DS(on)max}, I_D=-8.1\text{ A}$

¹¹⁾ 由设计指定, 未经过生产测试。

表7 动态特性 (N沟道)

Parameter	Symbol	Values			Unit	Note/ Test Condition
		Min.	Typ.	Max.		
Input capacitance ¹²⁾	C_{iss}	-	620	810	pF	$V_{GS}=0\text{ V}, V_{DS}=15\text{ V}, f=1\text{ MHz}$
Output capacitance ¹²⁾	C_{oss}	-	210	270	pF	$V_{GS}=0\text{ V}, V_{DS}=15\text{ V}, f=1\text{ MHz}$
Reverse transfer capacitance ¹²⁾	C_{rss}	-	18	32	pF	$V_{GS}=0\text{ V}, V_{DS}=15\text{ V}, f=1\text{ MHz}$
Turn-on delay time	$t_{d(on)}$	-	6.2	-	ns	$V_{DD}=15\text{ V}, V_{GS}=4.5\text{ V}, I_D=8.4\text{ A},$ $R_{G,ext}=1.6\text{ }\Omega$

表 7 动态特性 (N 沟道)

Parameter	Symbol	Values			Unit	Note/ Test Condition
		Min.	Typ.	Max.		
Rise time	t_r	-	3.4	-	ns	$V_{DD}=15\text{ V}, V_{GS}=4.5\text{ V}, I_D=8.4\text{ A}, R_{G,ext}=1.6\ \Omega$
Turn-off delay time	$t_{d(off)}$	-	5.8	-	ns	$V_{DD}=15\text{ V}, V_{GS}=4.5\text{ V}, I_D=8.4\text{ A}, R_{G,ext}=1.6\ \Omega$
Fall time	t_f	-	3.4	-	ns	$V_{DD}=15\text{ V}, V_{GS}=4.5\text{ V}, I_D=8.4\text{ A}, R_{G,ext}=1.6\ \Omega$
Gate to source charge	Q_{gs}	-	1.9	-	nC	$V_{DD}=15\text{ V}, I_D=8.4\text{ A}, V_{GS}=0\text{ to }4.5\text{ V}$
Gate charge at threshold	$Q_{g(th)}$	-	1.0	-	nC	$V_{DD}=15\text{ V}, I_D=8.4\text{ A}, V_{GS}=0\text{ to }4.5\text{ V}$
Gate to drain charge	Q_{gd}	-	1.0	-	nC	$V_{DD}=15\text{ V}, I_D=8.4\text{ A}, V_{GS}=0\text{ to }4.5\text{ V}$
Switching charge	Q_{sw}	-	1.9	-	nC	$V_{DD}=15\text{ V}, I_D=8.4\text{ A}, V_{GS}=0\text{ to }4.5\text{ V}$
Gate charge total ¹²⁾	Q_g	-	4.2	6.3	nC	$V_{DD}=15\text{ V}, I_D=8.4\text{ A}, V_{GS}=0\text{ to }4.5\text{ V}$
Gate plateau voltage	$V_{plateau}$	-	3.0	-	V	$V_{DD}=15\text{ V}, I_D=8.4\text{ A}, V_{GS}=0\text{ to }4.5\text{ V}$
Gate charge total ¹²⁾	Q_g	-	8.9	13.4	nC	$V_{DD}=15\text{ V}, I_D=8.4\text{ A}, V_{GS}=0\text{ to }10\text{ V}$
Output charge	Q_{oss}	-	4.8	-	nC	$V_{DS}=15\text{ V}, V_{GS}=0\text{ V}$

¹²⁾ 由设计指定, 未经过生产测试。

表 8 动态特性 (P 沟道)

Parameter	Symbol	Values			Unit	Note/ Test Condition
		Min.	Typ.	Max.		
Input capacitance ¹³⁾	C_{iss}	-	1100	1400	pF	$V_{GS}=0\text{ V}, V_{DS}=-15\text{ V}, f=1\text{ MHz}$
Output capacitance ¹³⁾	C_{oss}	-	490	640	pF	$V_{GS}=0\text{ V}, V_{DS}=-15\text{ V}, f=1\text{ MHz}$
Reverse transfer capacitance ¹³⁾	C_{rss}	-	36	63	pF	$V_{GS}=0\text{ V}, V_{DS}=-15\text{ V}, f=1\text{ MHz}$
Turn-on delay time	$t_{d(on)}$	-	12	-	ns	$V_{DD}=-15\text{ V}, V_{GS}=-4.5\text{ V}, I_D=-8.1\text{ A}, R_{G,ext}=1.6\ \Omega$
Rise time	t_r	-	8.1	-	ns	$V_{DD}=-15\text{ V}, V_{GS}=-4.5\text{ V}, I_D=-8.1\text{ A}, R_{G,ext}=1.6\ \Omega$
Turn-off delay time	$t_{d(off)}$	-	15	-	ns	$V_{DD}=-15\text{ V}, V_{GS}=-4.5\text{ V}, I_D=-8.1\text{ A}, R_{G,ext}=1.6\ \Omega$
Fall time	t_f	-	9.0	-	ns	$V_{DD}=-15\text{ V}, V_{GS}=-4.5\text{ V}, I_D=-8.1\text{ A}, R_{G,ext}=1.6\ \Omega$
Gate to source charge	Q_{gs}	-	-3.3	-	nC	$V_{DD}=-15\text{ V}, I_D=-8.1\text{ A}, V_{GS}=0\text{ to }-4.5\text{ V}$
Gate charge at threshold	$Q_{g(th)}$	-	-1.8	-	nC	$V_{DD}=-15\text{ V}, I_D=-8.1\text{ A}, V_{GS}=0\text{ to }-4.5\text{ V}$
Gate to drain charge	Q_{gd}	-	-1.8	-	nC	$V_{DD}=-15\text{ V}, I_D=-8.1\text{ A}, V_{GS}=0\text{ to }-4.5\text{ V}$
Switching charge	Q_{sw}	-	-3.4	-	nC	$V_{DD}=-15\text{ V}, I_D=-8.1\text{ A}, V_{GS}=0\text{ to }-4.5\text{ V}$
Gate charge total ¹³⁾	Q_g	-	-7.2	-10.8	nC	$V_{DD}=-15\text{ V}, I_D=-8.1\text{ A}, V_{GS}=0\text{ to }-4.5\text{ V}$

表 8 动态特性 (P 沟道)

Parameter	Symbol	Values			Unit	Note/ Test Condition
		Min.	Typ.	Max.		
Gate plateau voltage	V_{plateau}	-	-3	-	V	$V_{\text{DD}}=-15\text{ V}$, $I_{\text{D}}=-8.1\text{ A}$, $V_{\text{GS}}=0\text{ to }-4.5\text{ V}$
Gate charge total ¹³⁾	Q_{g}	-	-14.8	-22.2	nC	$V_{\text{DD}}=-15\text{ V}$, $I_{\text{D}}=-8.1\text{ A}$, $V_{\text{GS}}=0\text{ to }-10\text{ V}$
Output charge	Q_{oss}	-	-10.4	-	nC	$V_{\text{DS}}=-15\text{ V}$, $V_{\text{GS}}=0\text{ V}$

¹³⁾ 由设计指定, 未经过生产测试。

表 9 反向二极管 (N 沟道)

Parameter	Symbol	Values			Unit	Note/ Test Condition
		Min.	Typ.	Max.		
Diode continuous forward current	I_{S}	-	-	3.1	A	$T_{\text{A}}=25\text{ }^{\circ}\text{C}$
Diode pulse current	$I_{\text{S,pulse}}$	-	-	34	A	$T_{\text{A}}=25\text{ }^{\circ}\text{C}$
Diode forward voltage	V_{SD}	-	0.88	1.0	V	$V_{\text{GS}}=0\text{ V}$, $I_{\text{F}}=8.4\text{ A}$, $T_{\text{j}}=25\text{ }^{\circ}\text{C}$
Reverse recovery time	t_{rr}	-	12	-	ns	$V_{\text{R}}=15\text{ V}$, $I_{\text{F}}=8.4\text{ A}$, $di_{\text{F}}/dt=100\text{ A}/\mu\text{s}$
Reverse recovery charge	Q_{rr}	-	3.9	-	nC	$V_{\text{R}}=15\text{ V}$, $I_{\text{F}}=8.4\text{ A}$, $di_{\text{F}}/dt=100\text{ A}/\mu\text{s}$

表 10 反向二极管 (P 沟道)

Parameter	Symbol	Values			Unit	Note/ Test Condition
		Min.	Typ.	Max.		
Diode continuous forward current	I_{S}	-	-	-3.3	A	$T_{\text{A}}=25\text{ }^{\circ}\text{C}$
Diode pulse current	$I_{\text{S,pulse}}$	-	-	-32	A	$T_{\text{A}}=25\text{ }^{\circ}\text{C}$
Diode forward voltage	V_{SD}	-	-0.90	-1	V	$V_{\text{GS}}=0\text{ V}$, $I_{\text{F}}=-8.1\text{ A}$, $T_{\text{j}}=25\text{ }^{\circ}\text{C}$
Reverse recovery time	t_{rr}	-	17	-	ns	$V_{\text{R}}=-15\text{ V}$, $I_{\text{F}}=-8.1\text{ A}$, $di_{\text{F}}/dt=-100\text{ A}/\mu\text{s}$
Reverse recovery charge	Q_{rr}	-	6.2	-	nC	$V_{\text{R}}=-15\text{ V}$, $I_{\text{F}}=-8.1\text{ A}$, $di_{\text{F}}/dt=-100\text{ A}/\mu\text{s}$

4 电气特性图

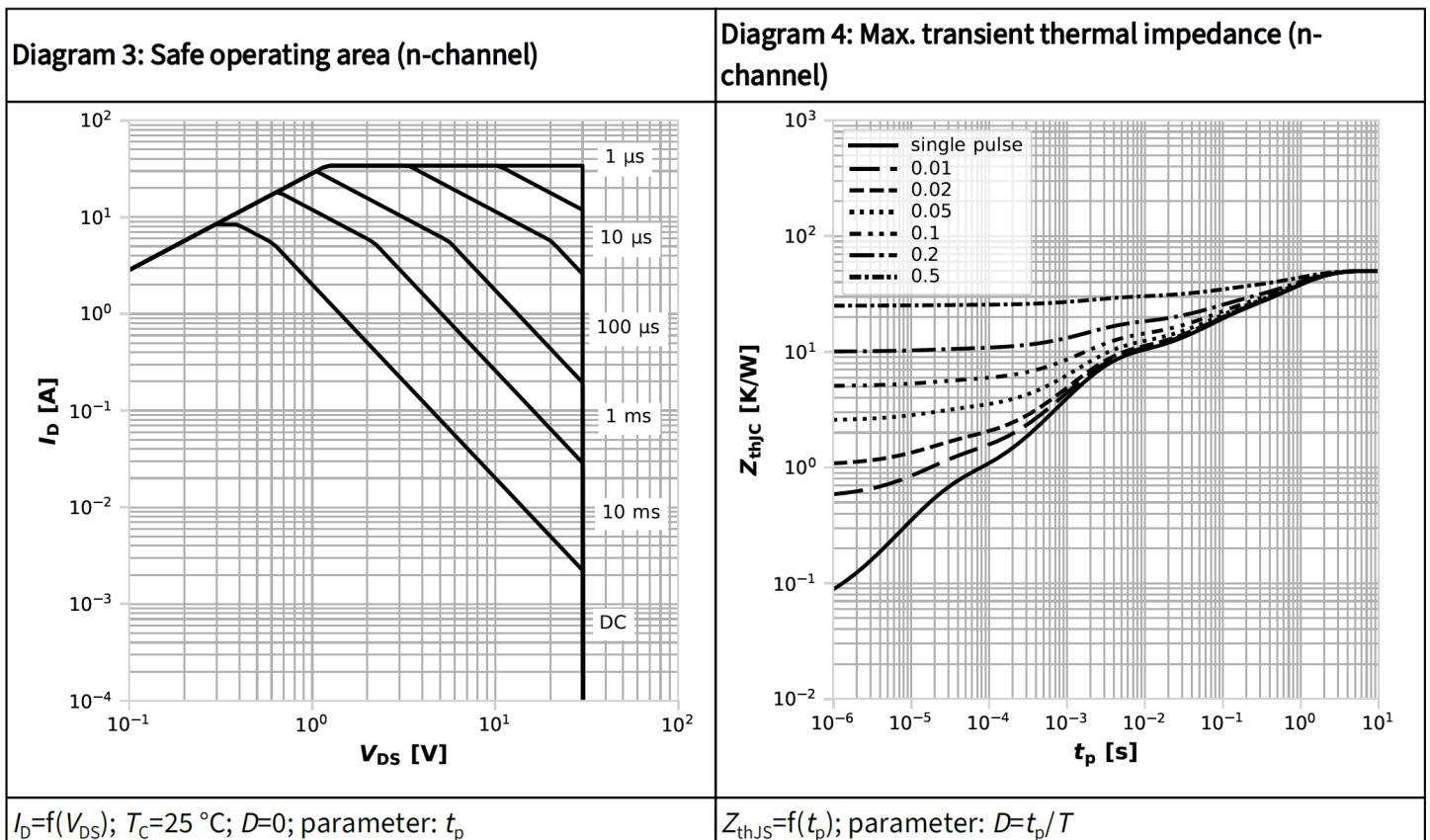
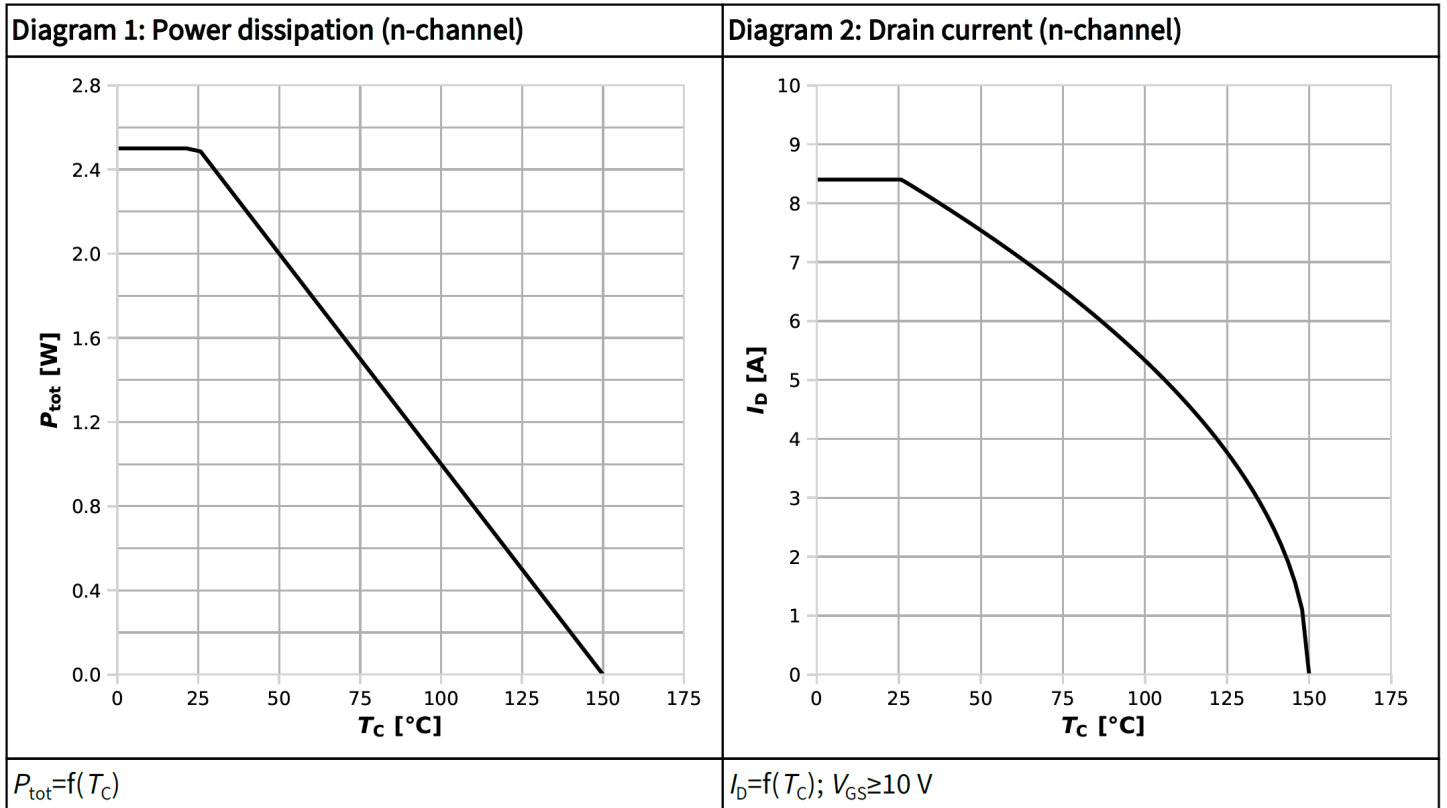
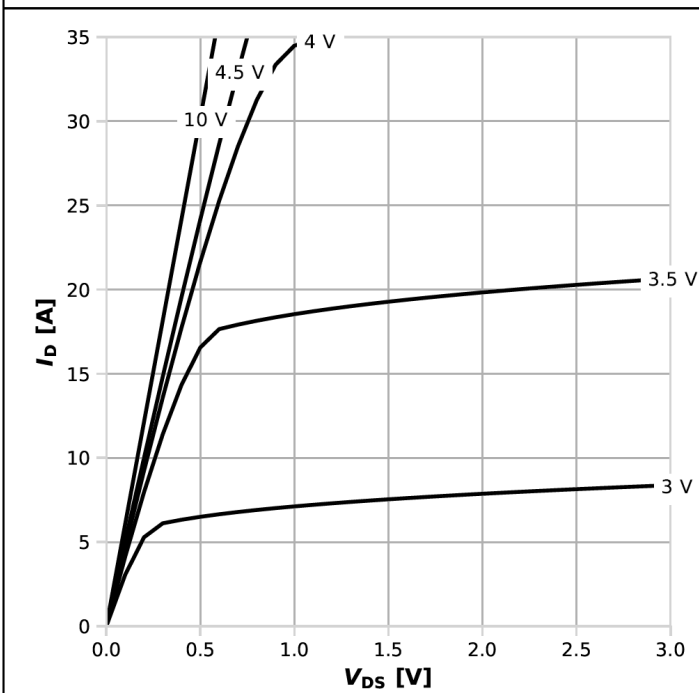
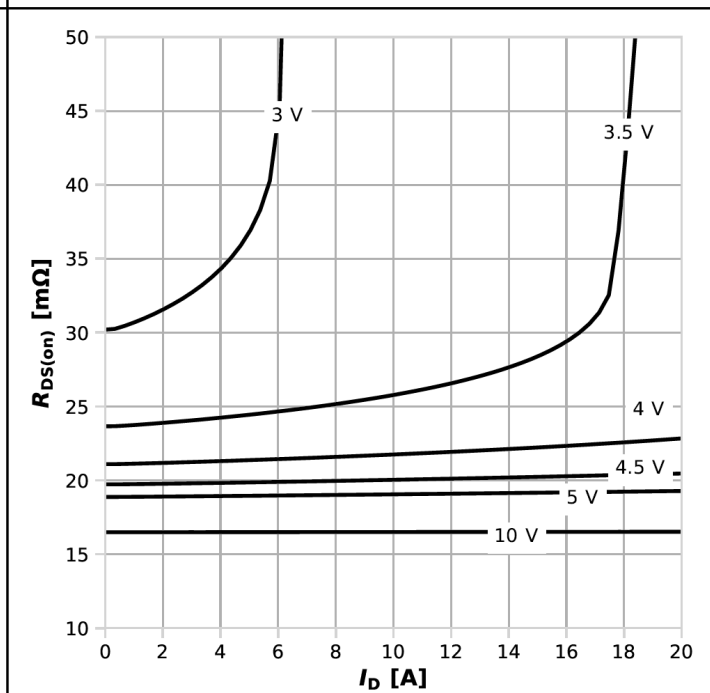


Diagram 5: Typ. output characteristics (n-channel)



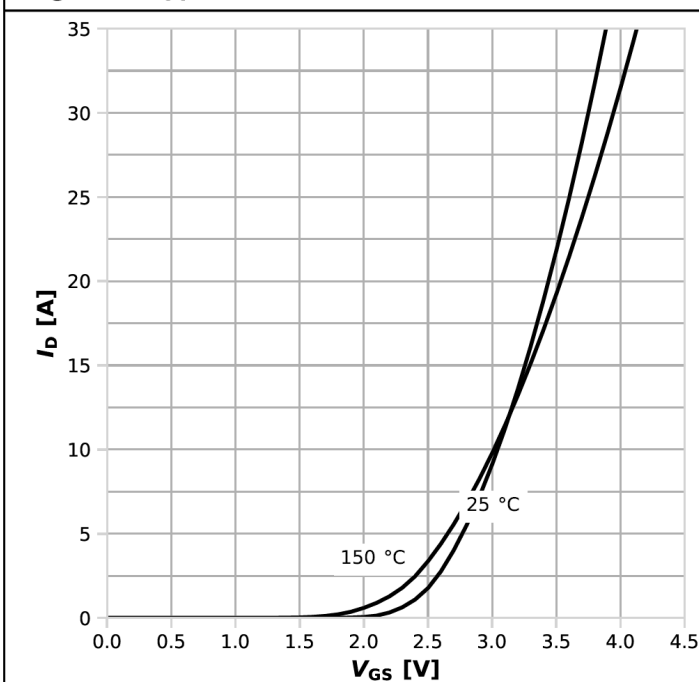
$$I_D = f(V_{DS}), T_j = 25^\circ\text{C}; \text{parameter: } V_{GS}$$

Diagram 6: Typ. drain-source on resistance (n-channel)



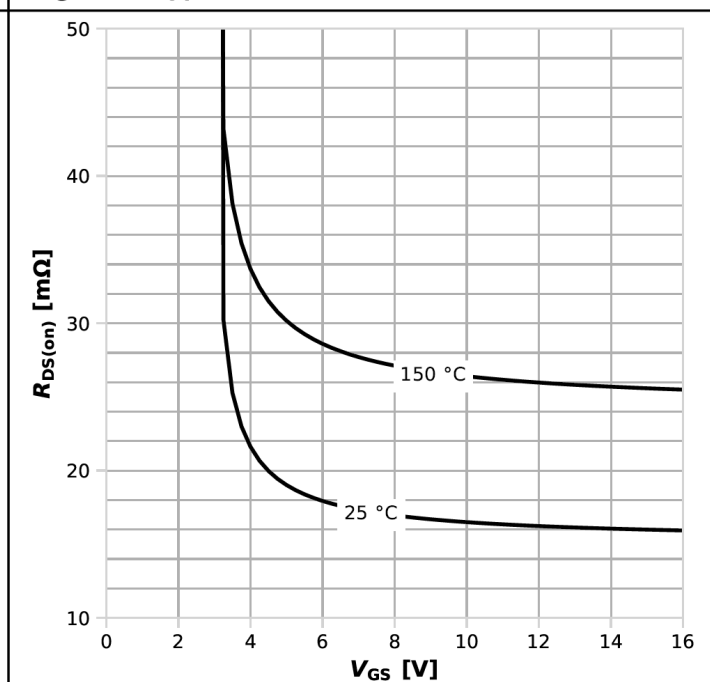
$$R_{DS(on)} = f(I_D), T_j = 25^\circ\text{C}; \text{parameter: } V_{GS}$$

Diagram 7: Typ. transfer characteristics (n-channel)



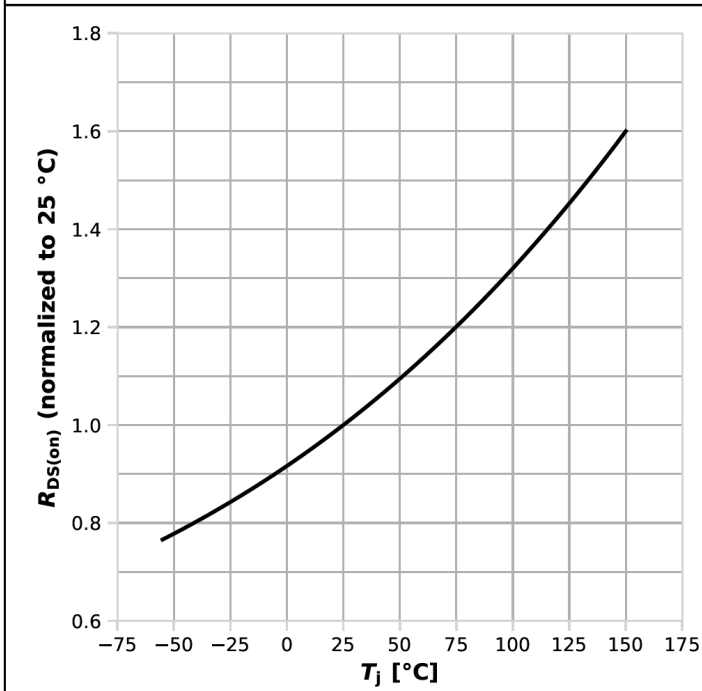
$$I_D = f(V_{GS}), |V_{DS}| > 2|I_D|R_{DS(on)max}; \text{parameter: } T_j$$

Diagram 8: Typ. drain-source on resistance (n-channel)



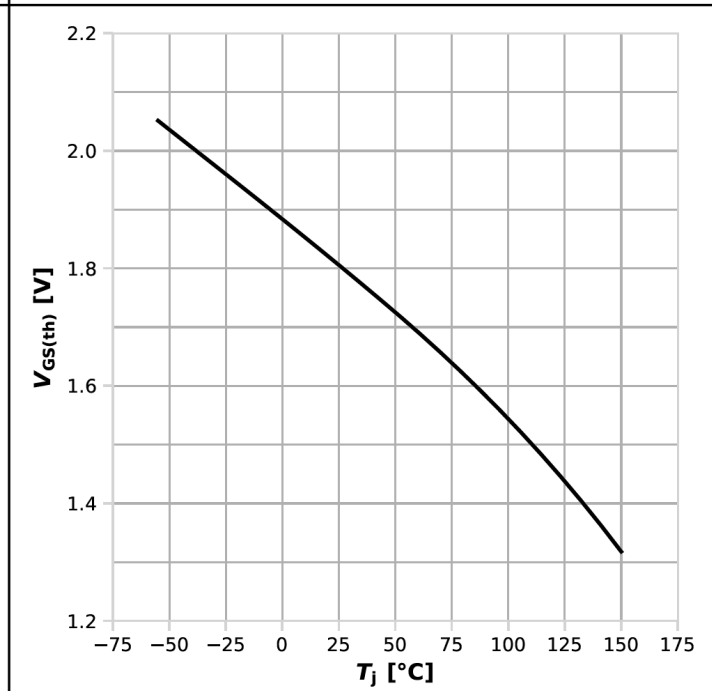
$$R_{DS(on)} = f(V_{GS}), I_D = 8.4\text{A}; \text{parameter: } T_j$$

Diagram 9: Normalized drain-source on resistance (n-channel)



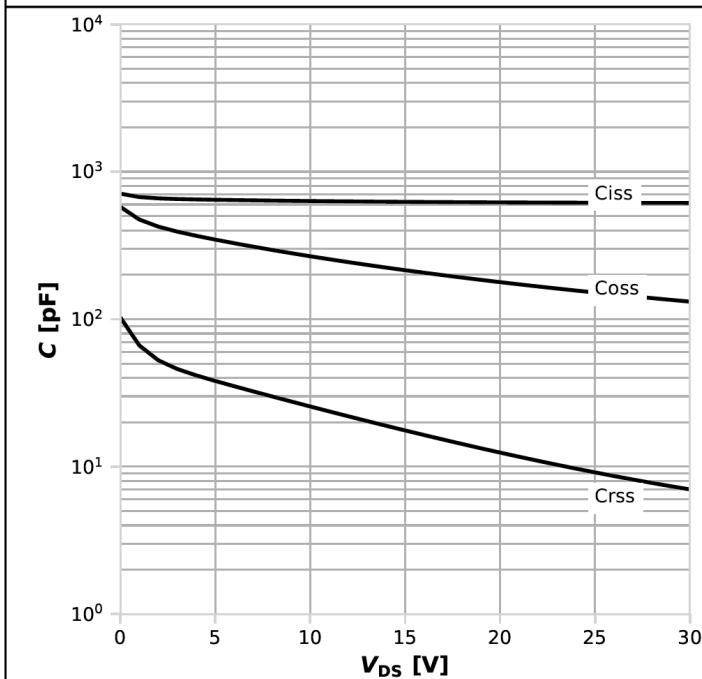
$$R_{DS(on)} = f(T_j), I_D = 8.4 \text{ A}, V_{GS} = 10 \text{ V}$$

Diagram 10: Typ. gate threshold voltage (n-channel)



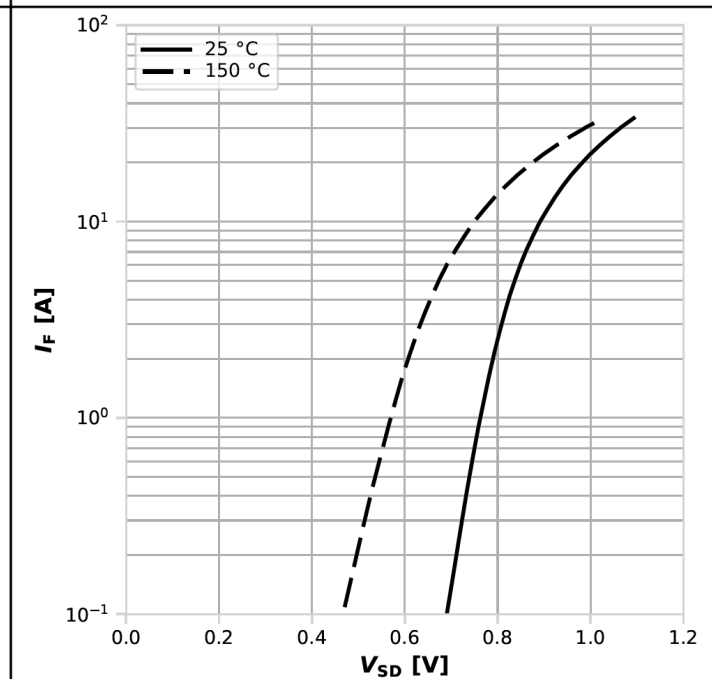
$$V_{GS(th)} = f(T_j), V_{GS} = V_{DS}, I_D = 1000 \mu\text{A}$$

Diagram 11: Typ. capacitances (n-channel)



$$C = f(V_{DS}); V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}$$

Diagram 12: Forward characteristics of reverse diode (n-ch.)



$$I_F = f(V_{SD}); \text{parameter: } T_j$$

Diagram 13: Avalanche characteristics (n-channel)

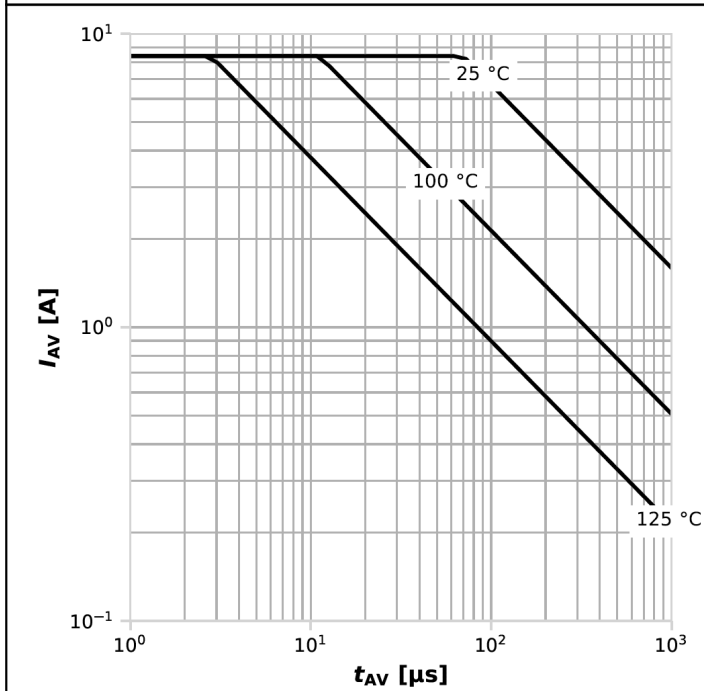

 $I_{AS}=f(t_{AV}); R_{GS}=25 \Omega; \text{parameter: } T_{j,start}$

Diagram 14: Typ. gate charge (n-channel)

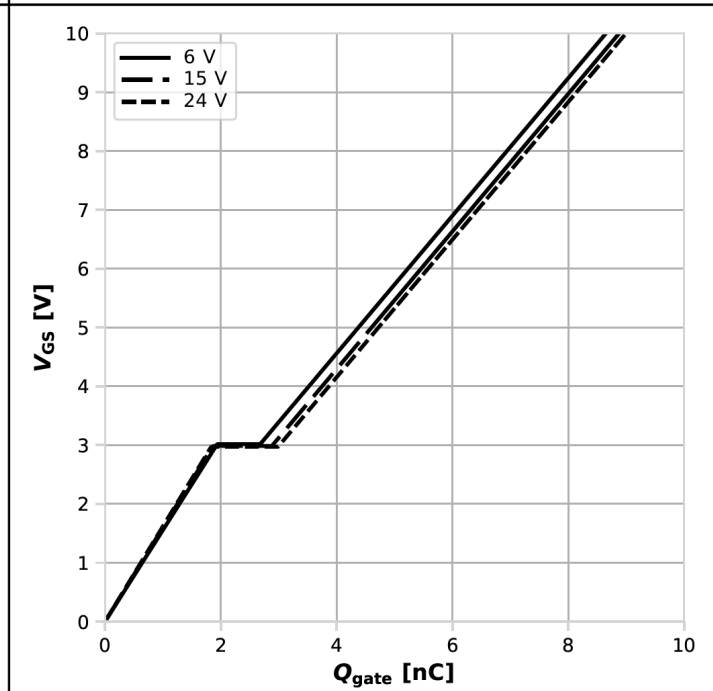

 $V_{GS}=f(Q_{gate}), I_D=8.4 \text{ A pulsed}, T_j=25 \text{ °C}; \text{parameter: } V_{DD}$

Diagram 15: Drain-source breakdown voltage (n-channel)

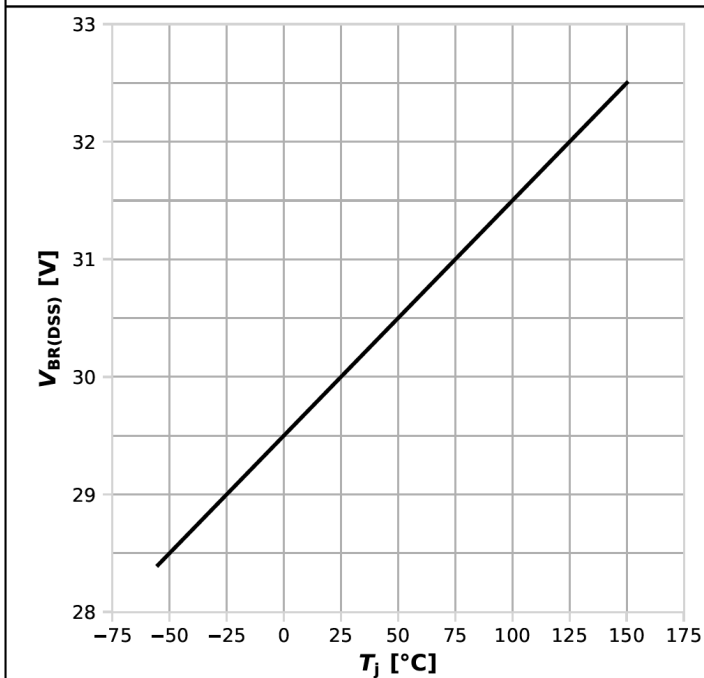

 $V_{BR(DSS)}=f(T_j); I_D=1 \text{ mA}$

Diagram 16: Power dissipation (p-channel)

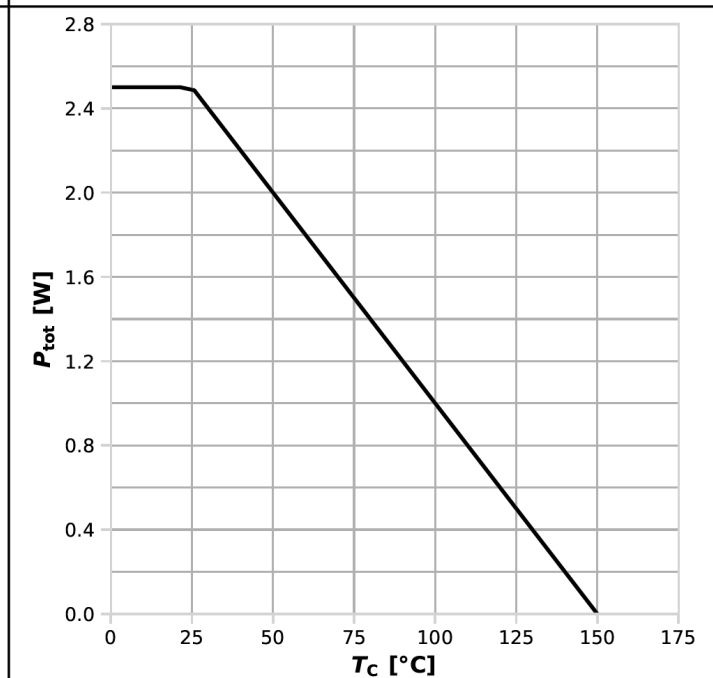
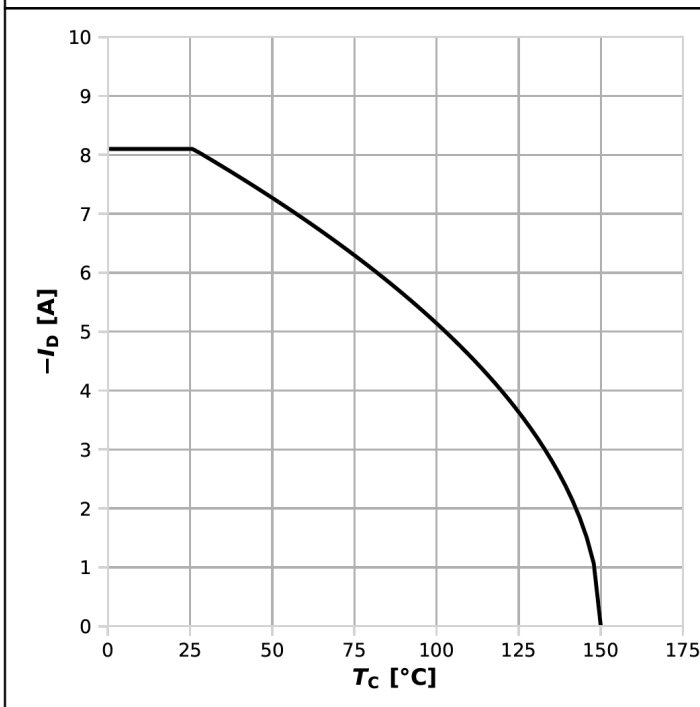
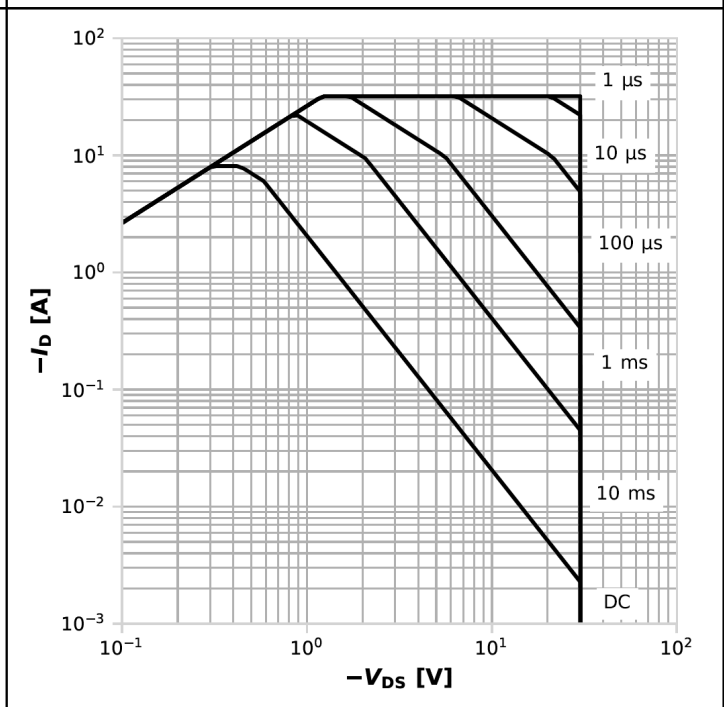

 $P_{tot}=f(T_c)$

Diagram 17: Drain current (p-channel)



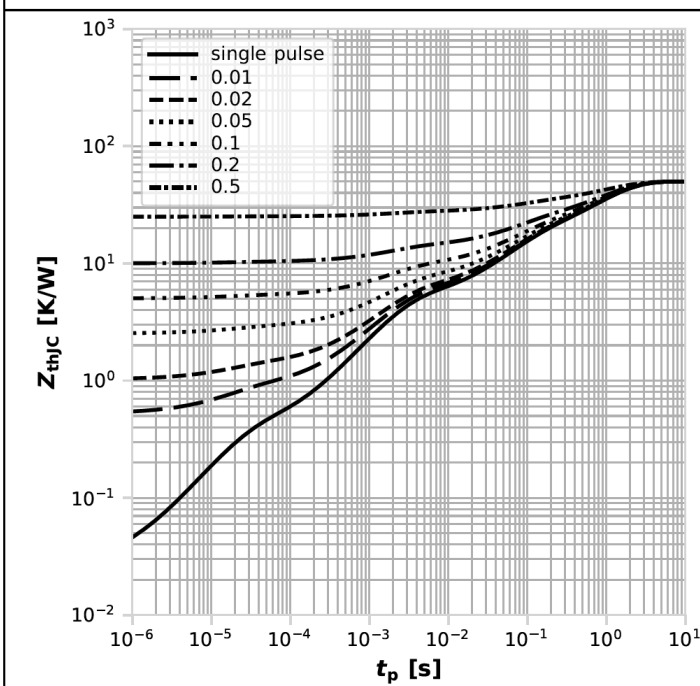
$I_D = f(T_C); |V_{GS}| \geq 10 \text{ V}$

Diagram 18: Safe operating area (p-channel)



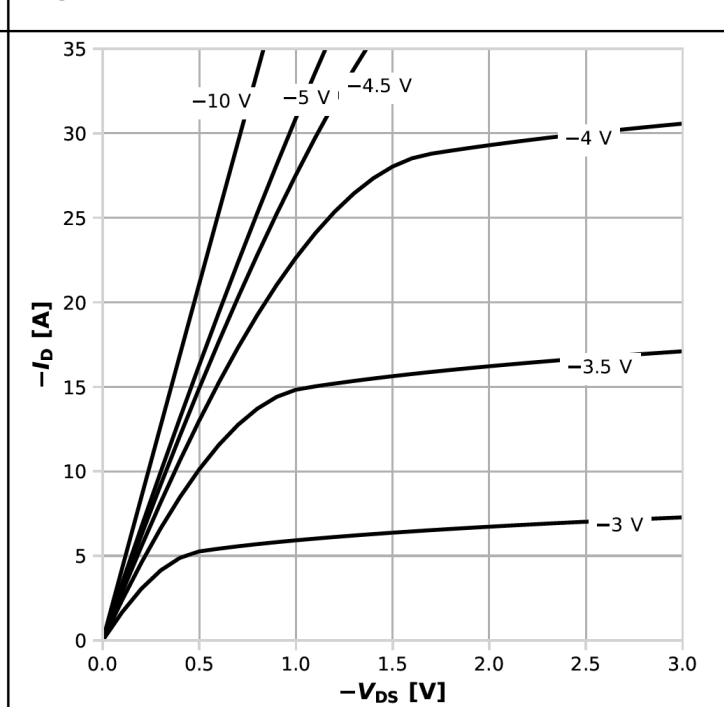
$I_D = f(V_{DS}); T_A = 25 \text{ °C}; D = 0; \text{parameter: } t_p$

Diagram 19: Max. transient thermal impedance (p-channel)



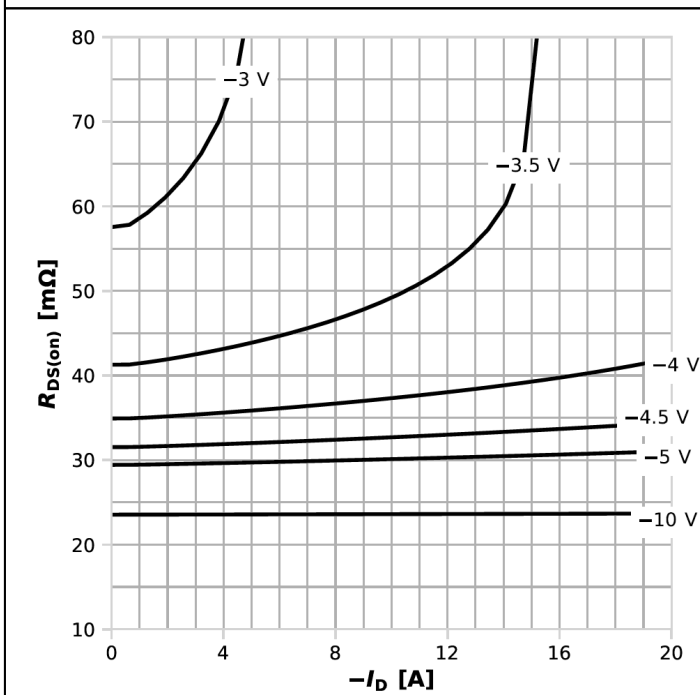
$Z_{thjC} = f(t_p); \text{parameter: } D = t_p / T$

Diagram 20: Typ. output characteristics (p-channel)



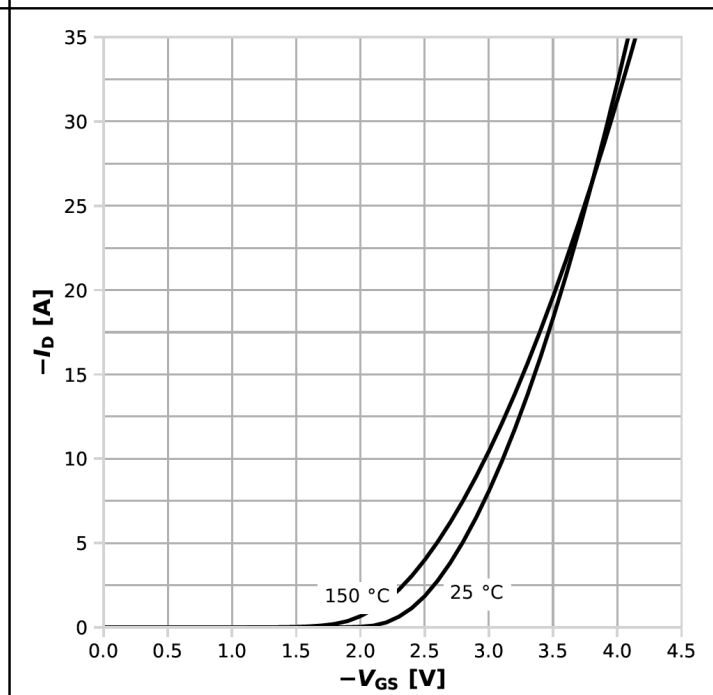
$I_D = f(V_{DS}); T_J = 25 \text{ °C}; \text{parameter: } V_{GS}$

Diagram 21: Typ. drain-source on resistance (p-channel)



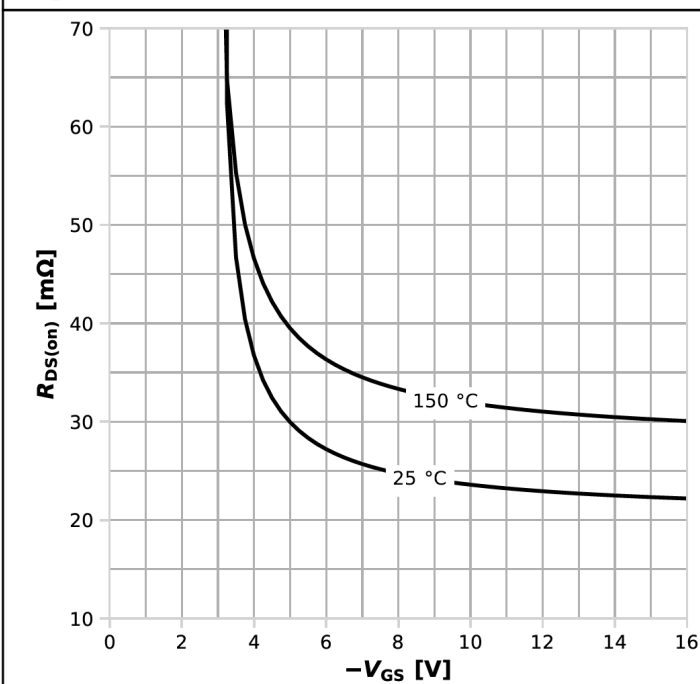
$$R_{DS(on)} = f(I_D), T_j = 25^\circ\text{C}; \text{parameter: } V_{GS}$$

Diagram 22: Typ. transfer characteristics (p-channel)



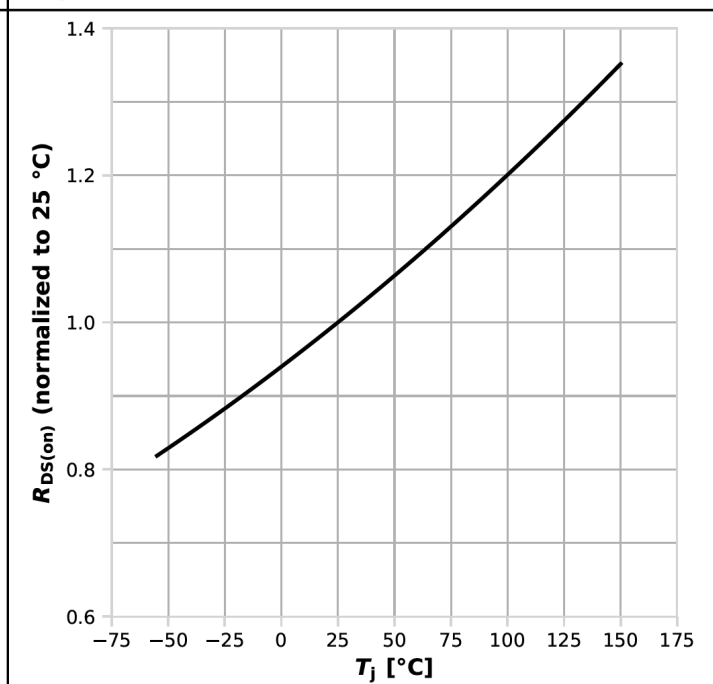
$$I_D = f(V_{GS}), |V_{DS}| > 2|I_D|R_{DS(on)max}; \text{parameter: } T_j$$

Diagram 23: Typ. drain-source on resistance (p-channel)



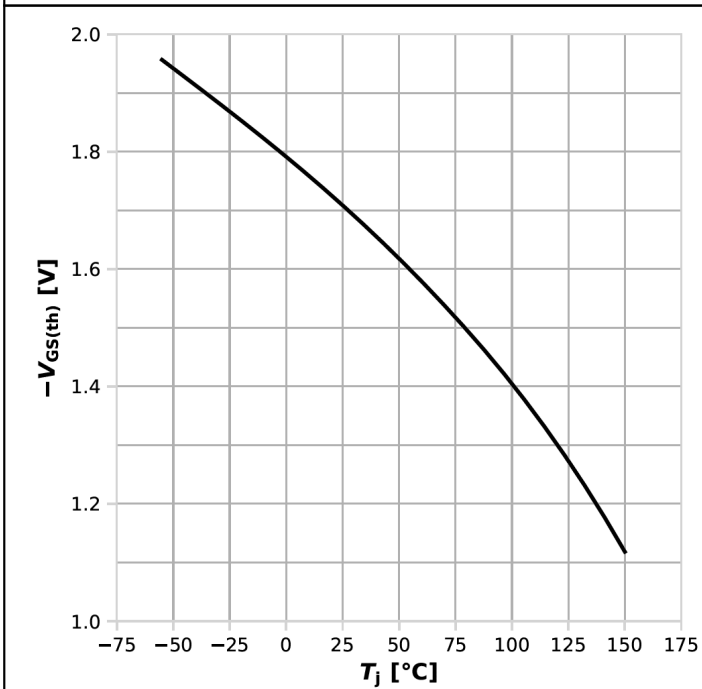
$$R_{DS(on)} = f(V_{GS}), I_D = -8.1 \text{ A}; \text{parameter: } T_j$$

Diagram 24: Normalized drain-source on resistance



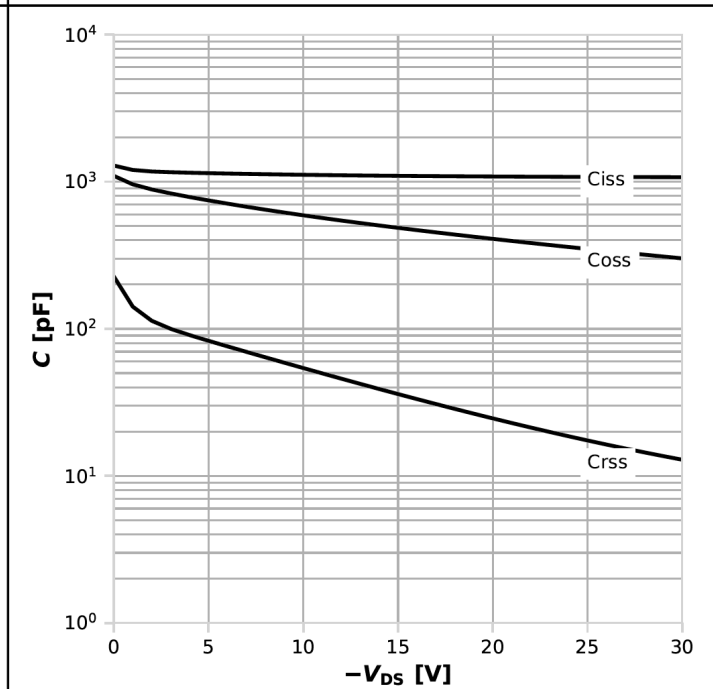
$$R_{DS(on)} = f(T_j), I_D = -8.1 \text{ A}, V_{GS} = -10 \text{ V}$$

Diagram 25: Typ. gate threshold voltage (p-channel)



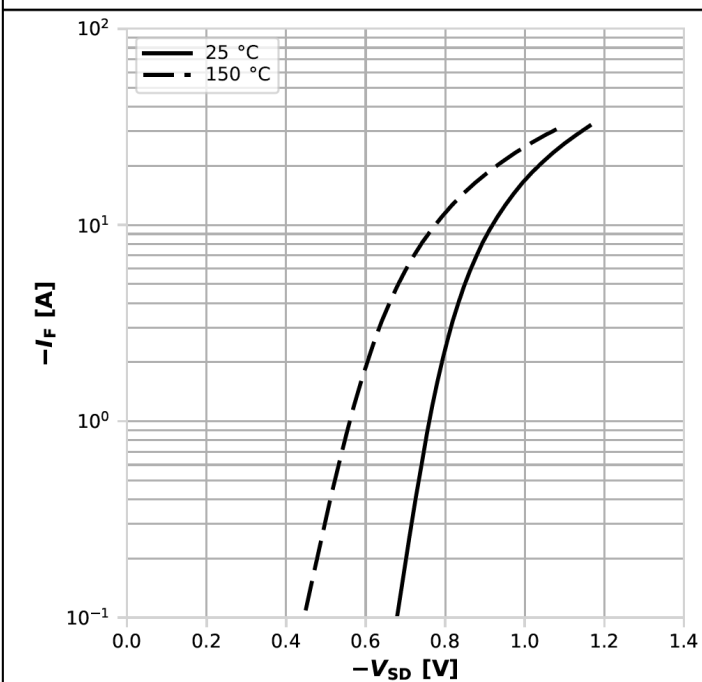
$$V_{GS(th)} = f(T_j), V_{GS} = V_{DS}, I_D = -1000 \mu A$$

Diagram 26: Typ. capacitances (p-channel)



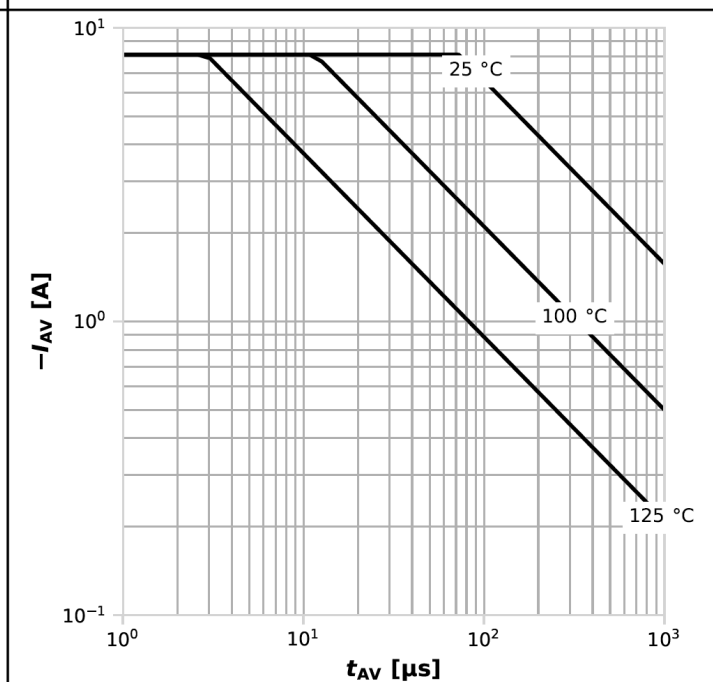
$$C = f(V_{DS}); V_{GS} = 0 V; f = 1 \text{ MHz}$$

Diagram 27: Forward characteristics of reverse diode (p-ch.)



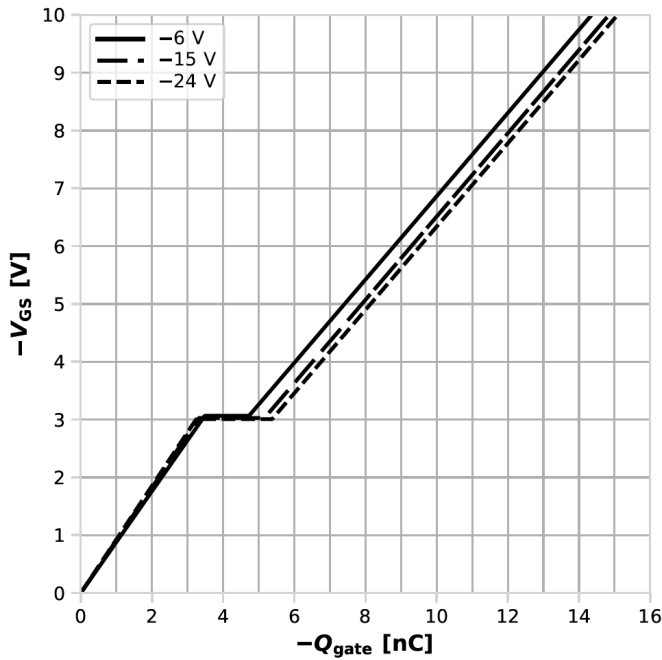
$$I_F = f(V_{SD}); \text{parameter: } T_j$$

Diagram 28: Avalanche characteristics (p-channel)



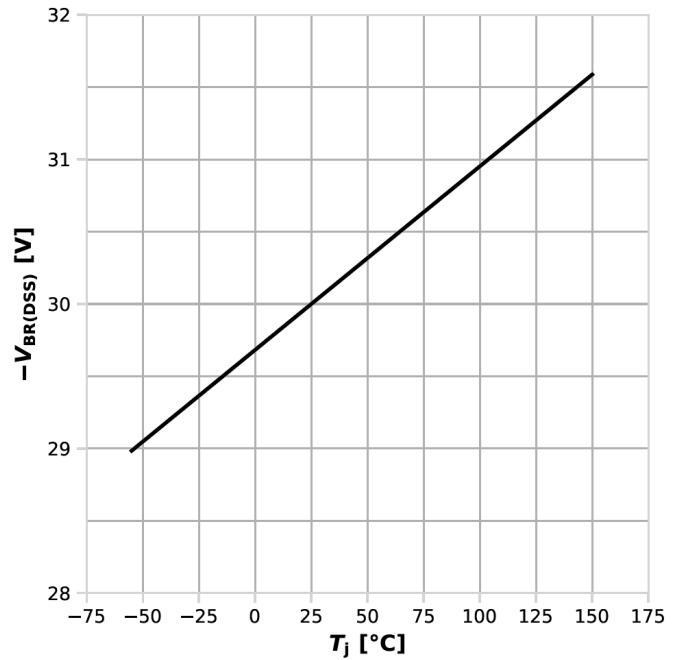
$$I_{AS} = f(t_{AV}); R_{GS} = 25 \Omega; \text{parameter: } T_{j,start}$$

Diagram 29: Typ. gate charge (p-channel)



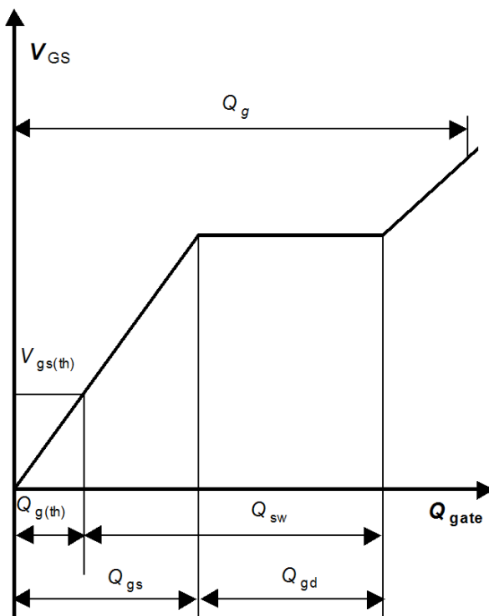
$V_{GS}=f(Q_{gate})$, $I_D=-8.1$ A pulsed, $T_j=25$ °C; parameter: V_{DD}

Diagram 30: Drain-source breakdown voltage (p-channel)

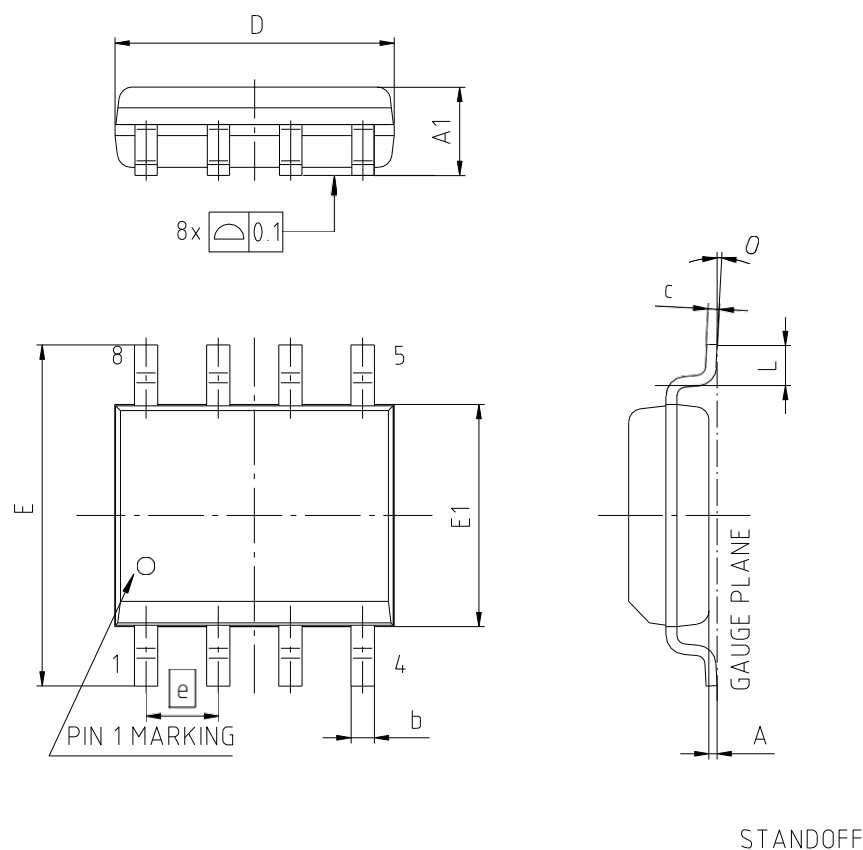


$V_{BR(DSS)}=f(T_j)$; $I_D=-1$ mA

Gate charge waveforms



5 封装外形



NOTE:

DIMENSIONS DO NOT INCLUDE MOLD FLASH, PROTRUSION OR GATE BURRS

图1 PG-TDSON-8外形图，尺寸单位为毫米

修订记录

ISA220280C03LMDS

Revision 2024 - 10 - 02, Rev. 2. 0

历史修订版本

Revision	Date	Subjects (major changes since last revision)
2.0	2024-10-02	Release of final datasheet

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版本 2025-12-24

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